

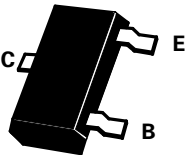
SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 2 – SEPTEMBER 95

BSS63

COMPLIMENTARY TYPE — BSS64

PARTMARKING DETAIL — BSS63 - T3
BSS63R - T6



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-110	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-6	V
Continuous Collector Current	I_C	-100	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{TOT}	330	mW
Operating and Storage Temperature Range	$t_j:t_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)}$	-110		V	$I_C = -10\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-100		V	$I_C = -100\mu A^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6		V	$I_E = -10\mu A$
Collector Cut-Off Current	I_{EBO}		-100 -50	nA μA	$V_{CB} = -90V$, $V_{CB} = -90V$, $T_{amb} = 150^{\circ}C$
Emitter Cut-Off Current	I_{EBO}		-200	nA	$V_{EB} = -6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-250	mV	$I_C = -25mA$, $I_B = -2.5mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-900	mV	$I_C = -25mA$, $I_B = -2.5mA$
Static Forward Current	h_{FE}	30 30			$I_C = -10mA$, $V_{CE} = -1V$ $I_C = 25mA$, $V_{CE} = 1V$
Transition Frequency	f_T	50	Typ 85	MHz	$V_{CE} = -5V$, $I_C = 25mA$ $f = 35 MHz$
Output Capacitance	C_{obo}		Typ. 3	pF	$V_{CB} = -10V$, $f = 1MHz$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$